



US 20230232639A1

(19) **United States**

(12) **Patent Application Publication**  
**MOSENDZ et al.**

(10) **Pub. No.: US 2023/0232639 A1**

(43) **Pub. Date: Jul. 20, 2023**

(54) **OVONIC THRESHOLD SWITCH  
SELECTORS WITH HIGH-CONDUCTIVITY  
CURRENT SPREADING LAYER**

**Publication Classification**

(51) **Int. Cl.**  
*H01L 27/24* (2006.01)  
*H01L 45/00* (2006.01)  
(52) **U.S. Cl.**  
CPC ..... *H01L 27/2427* (2013.01); *H01L 45/06*  
(2013.01); *H01L 45/144* (2013.01); *H01L*  
*45/1226* (2013.01)

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(21) Appl. No.: **17/579,147**

(22) Filed: **Jan. 19, 2022**

(57) **ABSTRACT**

A memory device includes a memory material portion, and an ovonic threshold switch selector element. The ovonic threshold switch selector element includes a first carbon-containing electrode comprising carbon and a metal, a second carbon-containing electrode comprising the carbon and the metal, and an ovonic threshold switch material portion located between the first electrode and the second electrode.

